

FIG. 1

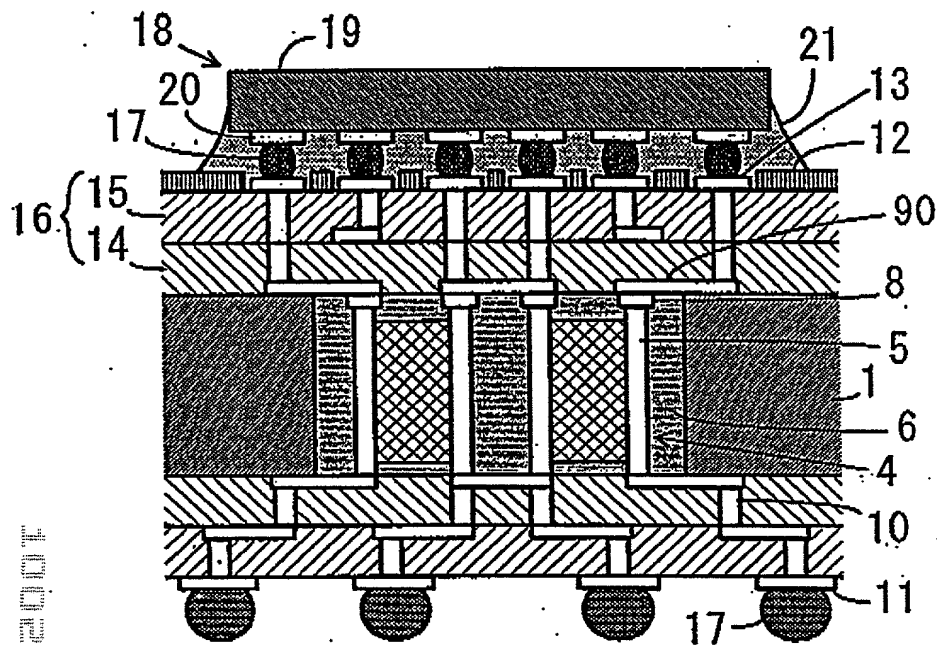


FIG. 2

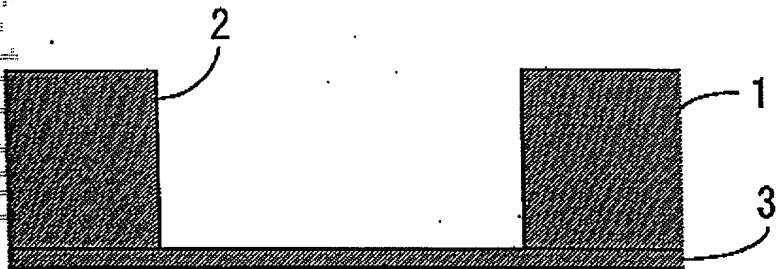


FIG. 3

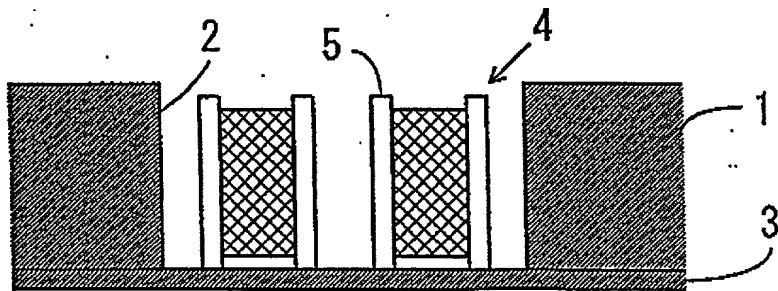


FIG. 4

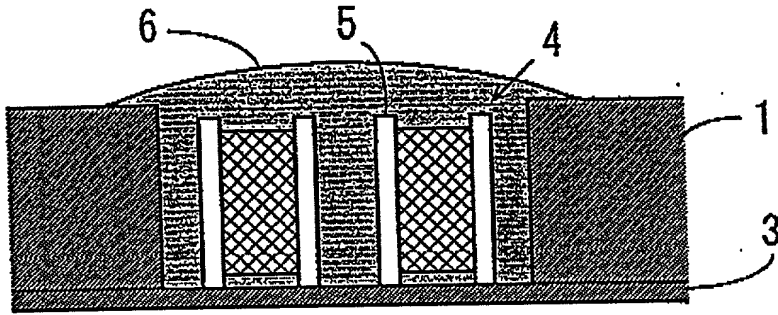


FIG. 5

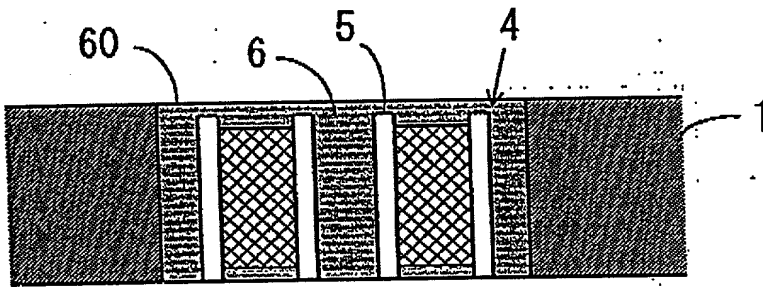


FIG. 6

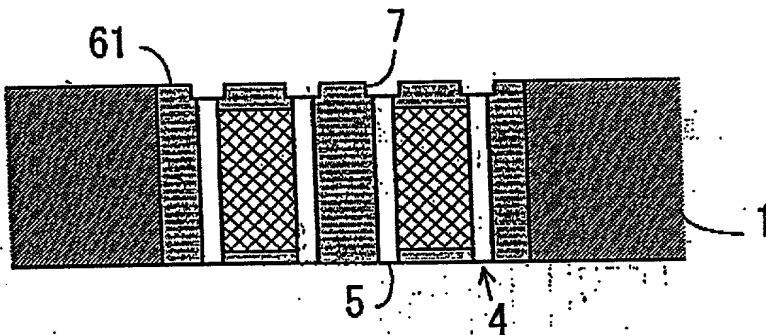


FIG. 7

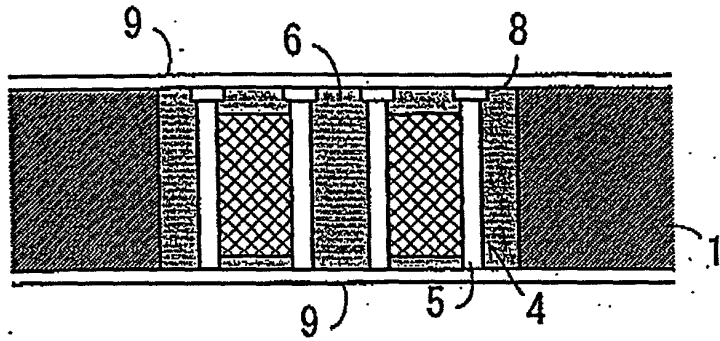


FIG. 8

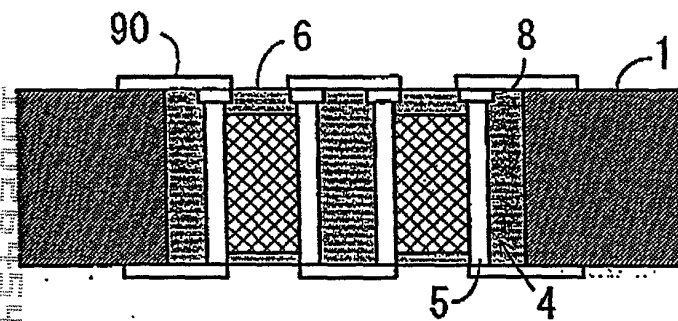
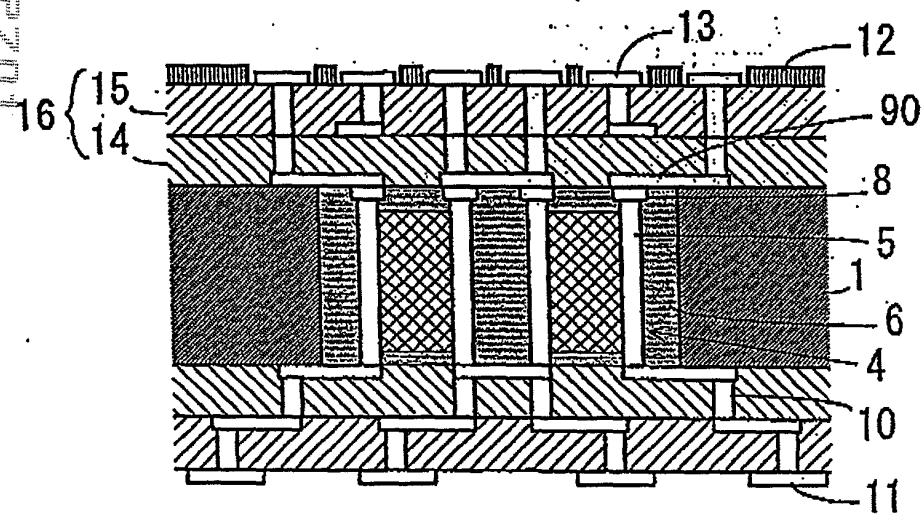


FIG. 9



A detailed cross-sectional diagram of a semiconductor device. The structure consists of several stacked layers. At the top is a layer labeled 270, followed by a patterned layer 280. Below this is a thick layer 300. A series of small rectangular features are embedded in a layer 290, which sits atop a layer 220. Beneath layer 220 is a complex structure featuring a central core 700 flanked by regions 900 and 1000. This core is supported by a base layer 170. To the right, there's another set of layers including 201, 210, 190, 400, 800, 200, and 100. A bottom-most layer is labeled 230. From the bottom of the device, four vertical pins or leads extend downwards, labeled 160, 140, 150, and 130. Other labels include 240, 260, and 250 pointing to various structural elements at the base.

FIG.12

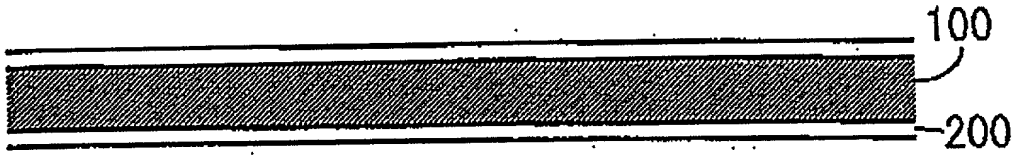


FIG.13

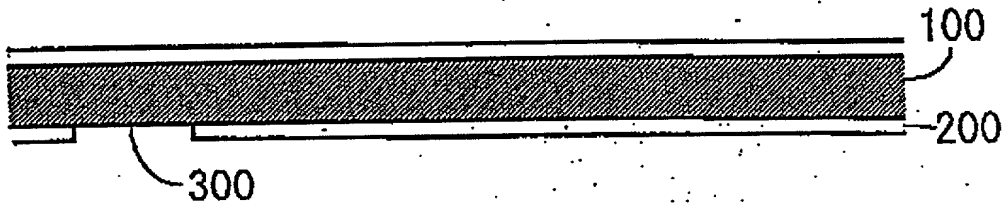


FIG.14

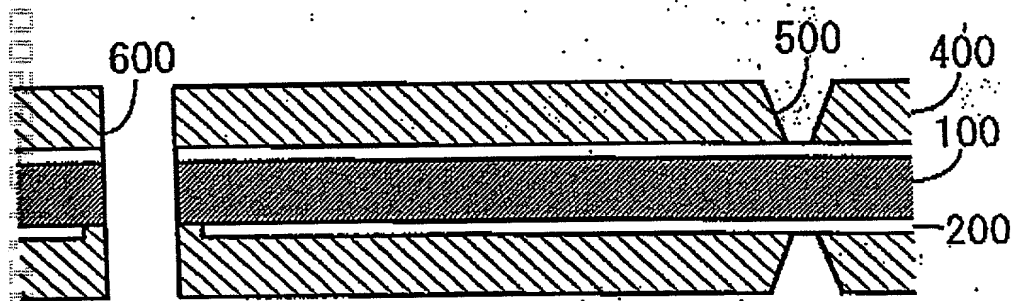


FIG.15

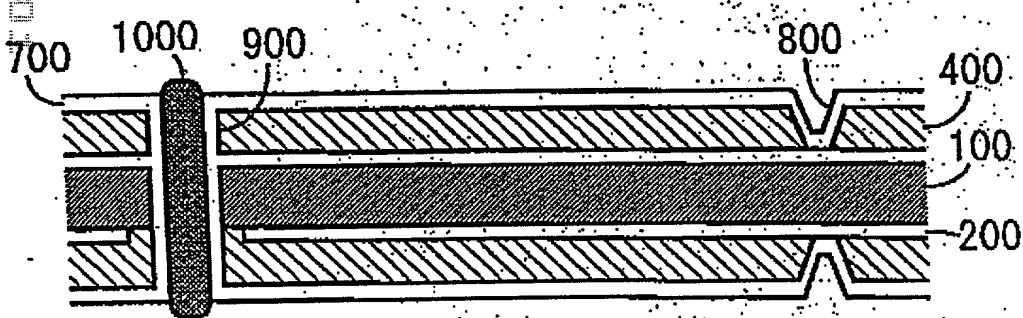


FIG. 16

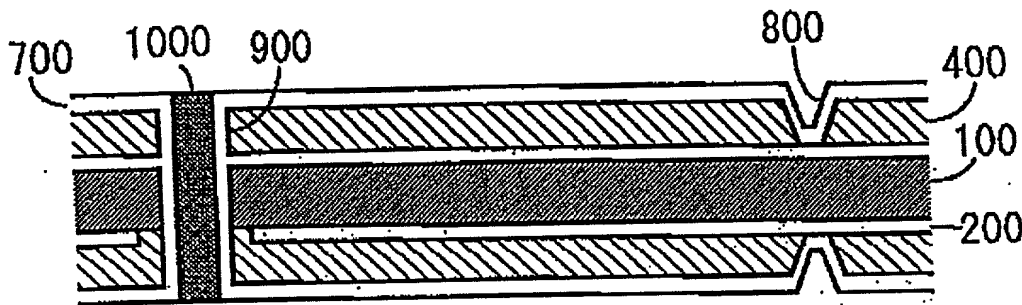


FIG. 17

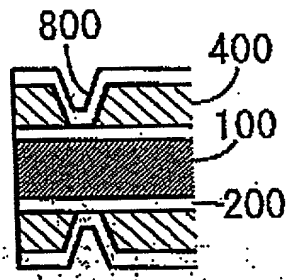
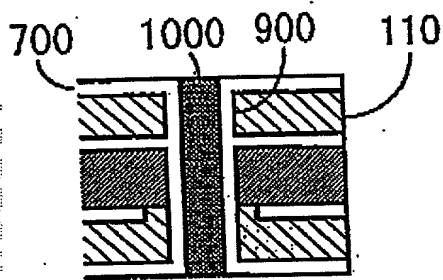


FIG. 18

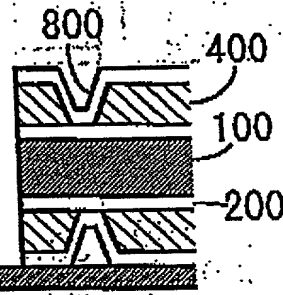
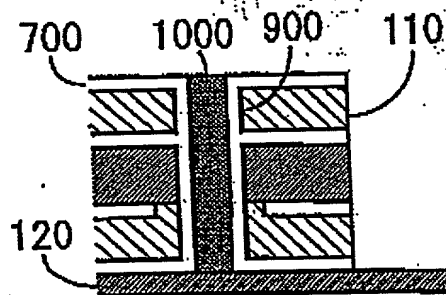


FIG. 19

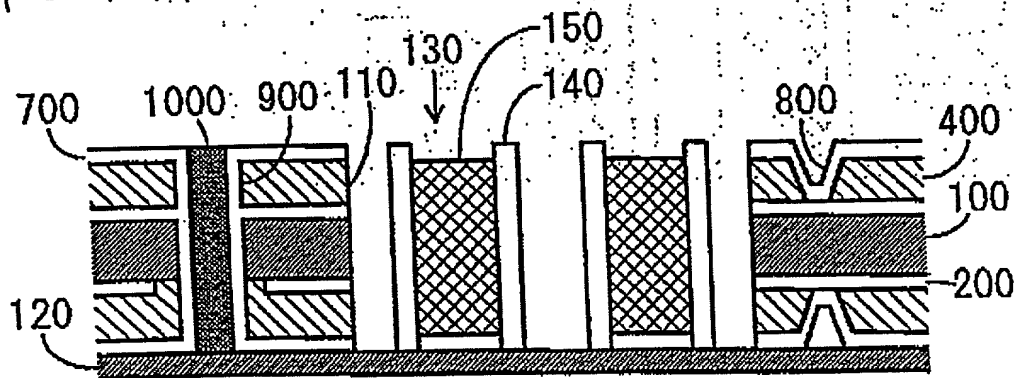


FIG. 20

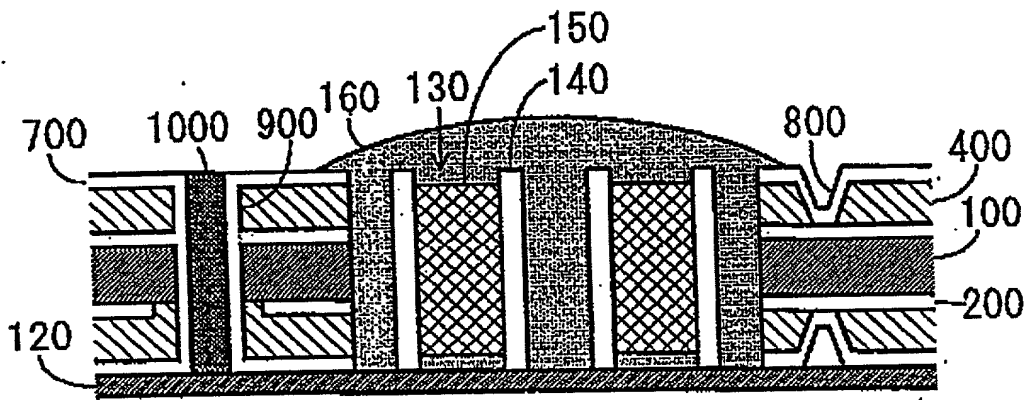


FIG. 21

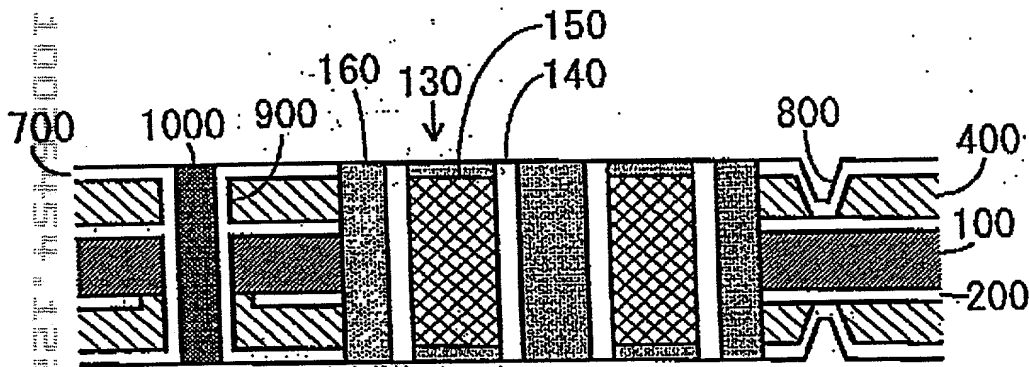


FIG. 22

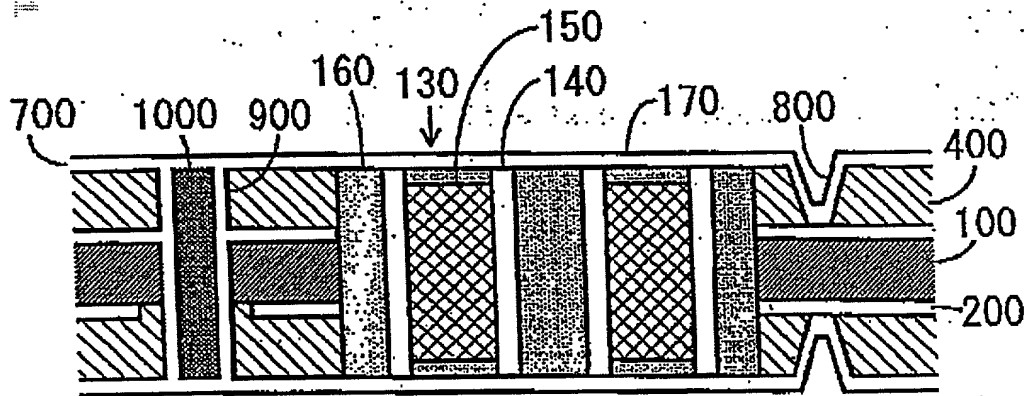


FIG. 23

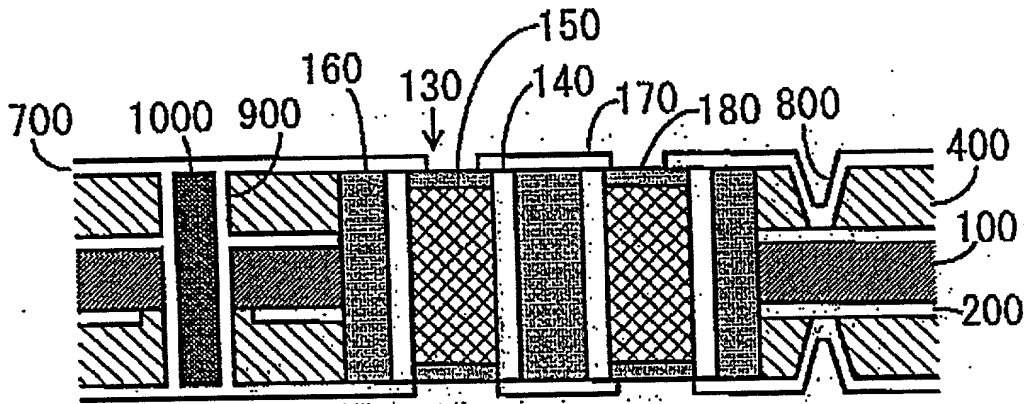


FIG. 24

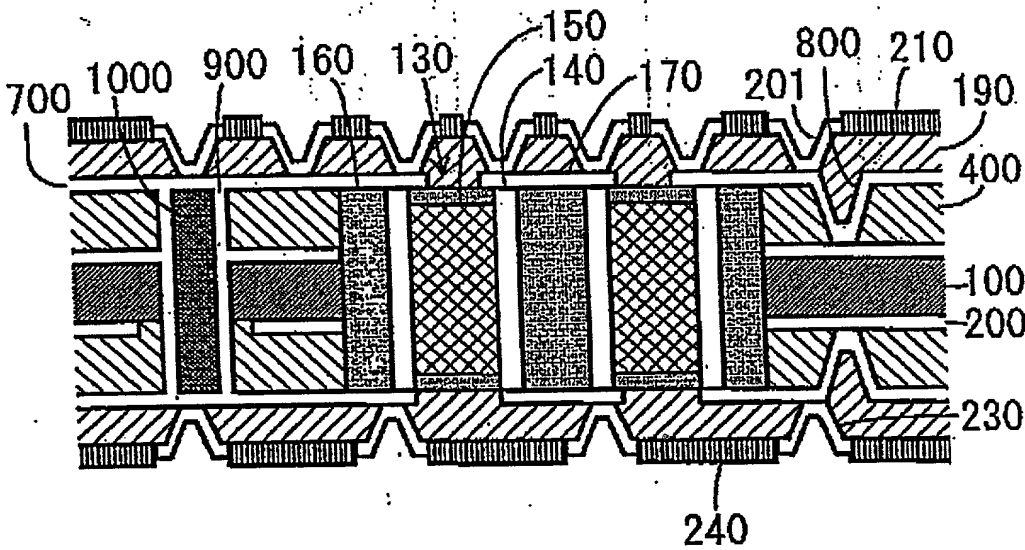




FIG. 25

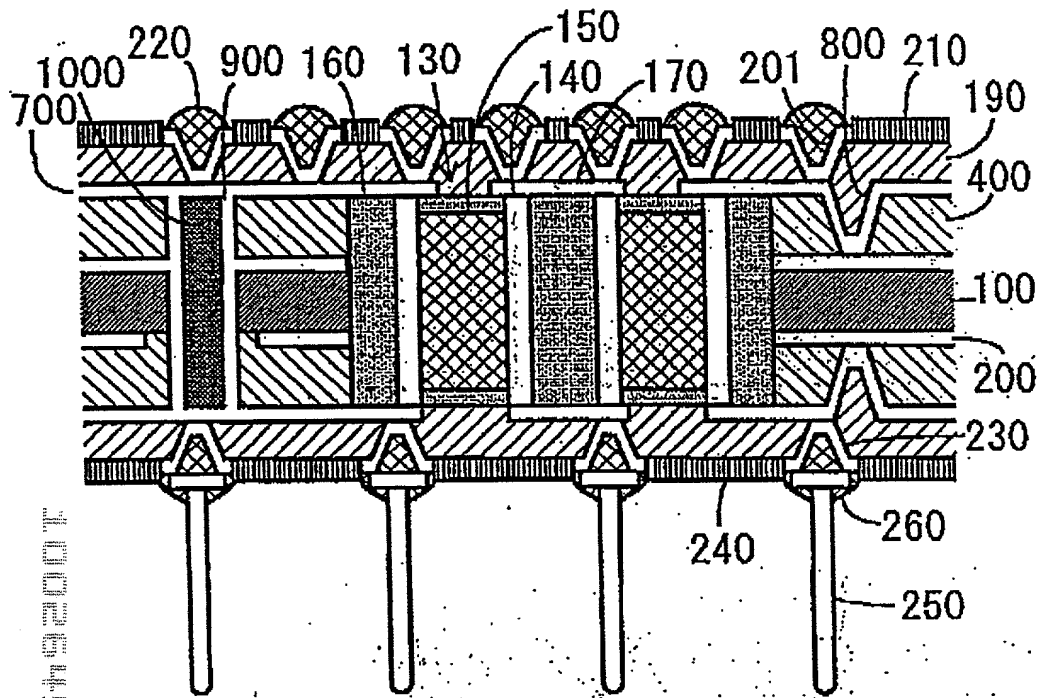


FIG. 25